

## List of Figures

<b>CHAPTER II</b>	<b>Pages</b>
<b>Equipments used and Details of the Experimentals</b>	<b>34-67</b>
<b>2.1 Construction of gap type cell configuration (Al/CdSe/Al structure)</b>	
<b>(a) Empty glass substrate</b>	<b>37</b>
<b>(b) Glass substrate with aluminium electrodes</b>	<b>37</b>
<b>(c) Glass substrate with aluminium electrodes and CdSe thin film for gap type cell configuration</b>	<b>37</b>
<b>2.2 CdSe thin film on glass substrate used for</b>	
<b>(a) XRD analysis</b>	<b>39</b>
<b>(b) SEM analysis</b>	<b>39</b>
<b>(c) thickness measurement</b>	<b>39</b>
<b>2.3 Schematic diagram of arrangement of masks</b>	<b>42</b>
<b>2.4(a) Arrangement for fringes of equal thickness</b>	<b>50</b>
<b>2.4(b) Interference fringes of equal thickness with fringe displacement</b>	<b>50</b>
<b>2.5 Optical arrangement of multiple beam interferometry method</b>	<b>51</b>
<b>2.6 Schematic diagram of sample holder</b>	<b>54</b>
<b>2.7 Arrangements of glass jacket, with sample holder inside, used for optoelectronic measurements</b>	<b>57</b>
<b>2.8 Block diagram of the experimental set up used for optoelectronic measurements</b>	<b>60</b>
<b>2.9 Optical focusing arrangement used for the illumination of sample</b>	<b>60</b>
<b>Photo Section :</b>	<b>62-64</b>
<b>Plate 1. Distillated water plant</b>	<b>62</b>
<b>Plate 2. Ultrasonic cleaning bath</b>	<b>62</b>
<b>Plate 3. Vacuum coating unit (12A4)</b>	<b>63</b>
<b>Plate 4. Assembled multiple beam interferometer</b>	<b>64</b>
<b>Plate 5. Sample holder</b>	<b>64</b>

## CHAPTER III

### Structural Characterization of CdSe Thin Films

68-113

3.1	XRD of bulk Cadmium Selenide (CdSe) sample	76
3.2(a)	NR plot of CdSe bulk sample for lattice parameter, a	77
3.2(b)	NR plot of CdSe bulk sample for lattice parameter, c	77
3.3(a)	XRD of a CdSe thin film ( $t = 2000\text{\AA}$ ) grown at $T_s = 623\text{K}$	80
3.3(b)	XRD of a CdSe thin film ( $t = 2000\text{\AA}$ ) grown at $T_s = 573\text{K}$	80
3.3(c)	XRD of a CdSe thin film ( $t = 2000\text{\AA}$ ) grown at $T_s = 523\text{K}$	81
3.3(d)	XRD of a CdSe thin film ( $t = 2000\text{\AA}$ ) grown at $T_s = 473\text{K}$	81
3.4	XRD of a CdSe thin film ( $t = 2000\text{\AA}$ ) grown at $T_s = 300\text{K}$	82
3.5(a)	XRD of a CdSe thin film ( $t = 2230\text{\AA}$ ) grown at $T_s = 473\text{K}$	82
3.5(b)	XRD of a CdSe thin film ( $t = 1750\text{\AA}$ ) grown at $T_s = 473\text{K}$	83
3.6(a)	FWHM of [002] peak of a CdSe film ( $t = 1750\text{\AA}$ ) grown at $T_s = 473\text{K}$	83
3.5(c)	XRD of a CdSe thin film ( $t = 1530\text{\AA}$ ) grown at $T_s = 473\text{K}$	84
3.6(b)	FWHM of [002] peak of a CdSe film ( $t = 1530\text{\AA}$ ) grown at $T_s = 473\text{K}$	84
3.5(d)	XRD of a CdSe thin film ( $t = 1000\text{\AA}$ ) grown at $T_s = 473\text{K}$	85
3.6(c)	FWHM of [002] peak of a CdSe film ( $t = 1000\text{\AA}$ ) grown at $T_s = 473\text{K}$	85
3.7(a)	NR plot of a CdSe thin film ( $t = 2000\text{\AA}$ , $T_s = 573\text{K}$ ) for lattice constant, a	86
3.7(b)	NR plot of a CdSe thin film ( $t = 2000\text{\AA}$ , $T_s = 573\text{K}$ ) for lattice constant, c	86
3.7(c)	NR plot of a CdSe thin film ( $t = 2000\text{\AA}$ , $T_s = 473\text{K}$ ) for lattice constant, a	87
3.7(d)	NR plot of a CdSe thin film ( $t = 2000\text{\AA}$ , $T_s = 473\text{K}$ ) for lattice constant, c	87
3.7(e)	NR plot of a CdSe thin film ( $t = 2230\text{\AA}$ , $T_s = 473\text{K}$ ) for lattice constant, a	88
3.7(f)	NR plot of a CdSe thin film ( $t = 2230\text{\AA}$ , $T_s = 473\text{K}$ ) for lattice constant, c	88
3.7(g)	NR plot of a CdSe thin film ( $t = 1750\text{\AA}$ , $T_s = 473\text{K}$ ) for lattice constant, a	89
3.7(h)	NR plot of a CdSe thin film ( $t = 1750\text{\AA}$ , $T_s = 473\text{K}$ ) for lattice constant, c	89
3.7(i)	NR plot of a CdSe thin film ( $t = 1530\text{\AA}$ , $T_s = 473\text{K}$ ) for lattice constant, a	90
3.7(j)	NR plot of a CdSe thin film ( $t = 1530\text{\AA}$ , $T_s = 473\text{K}$ ) for lattice constant, c	90
3.8(a)	Variation of grain size (D) with $T_s$ , of CdSe thin films of $t = 2000\text{\AA}$	91
3.8(b)	Variation of lattice constant, a, with $T_s$ , of CdSe thin films of $t = 2000\text{\AA}$	91
3.8(c)	Variation of lattice constant, c, with $T_s$ , of CdSe thin films of $t = 2000\text{\AA}$	92

<b>3.8(d) Variation of strain (<math>\epsilon</math>) with <math>T_s</math>, of CdSe thin films of constant <math>t = 2000\text{\AA}</math></b>	<b>92</b>
<b>3.9(a) Variation of lattice constant, <math>a</math>, with thickness of CdSe thin films grown at elevated <math>T_s = 473\text{K}</math></b>	<b>93</b>
<b>3.9(b) Variation of lattice constant, <math>c</math>, with thickness of CdSe thin films grown at elevated <math>T_s = 473\text{K}</math></b>	<b>93</b>
<b>3.9(c) Variation of grain size (<math>D</math>) with film thickness of CdSe thin films (<math>t</math>) grown at elevated <math>T_s = 473\text{K}</math></b>	<b>94</b>
<b>3.9(d) Variation of strain (<math>\epsilon</math>) with film thickness of CdSe thin films grown at elevated <math>T_s = 473\text{K}</math></b>	<b>94</b>
<b>3.10(a) Variation of strain with grain size (<math>D</math>) of CdSe thin films of <math>t = 2000\text{\AA}</math> and grown at different <math>T_s</math></b>	<b>99</b>
<b>3.10(b) Variation of strain with grain size (<math>D</math>) of CdSe thin films of different, <math>t</math> and deposited at <math>T_s = 473\text{K}</math></b>	<b>99</b>
<b>3.11(a) Variation of dislocation density with <math>T_s(\text{K})</math> of CdSe thin films of constant <math>t = 2000\text{\AA}</math></b>	<b>100</b>
<b>3.11(b) Variation of dislocation density with <math>t(\text{\AA})</math> of CdSe thin films grown at <math>T_s = 473\text{K}</math></b>	<b>100</b>
<b>3.12(a) Variation of dislocation density with strain of CdSe thin films of constant <math>t = 2000\text{\AA}</math> grown at different <math>T_s</math></b>	<b>101</b>
<b>3.12(b) Variation of dislocation density with strain of CdSe thin films of different thickness grown at <math>T_s = 473\text{K}</math></b>	<b>101</b>
<b>3.13(a) SEM photograph of a CdSe thin film of <math>t = 2000\text{\AA}</math> deposited at <math>T_s = 473\text{K}</math> (Magnification 9.42kX)</b>	<b>103</b>
<b>3.13(b) SEM photograph of a CdSe thin film of <math>t = 2000\text{\AA}</math> deposited at <math>T_s = 473\text{K}</math> (Magnification 12.14kX)</b>	<b>103</b>
<b>3.13(c) SEM photograph of a CdSe thin film of <math>t = 2000\text{\AA}</math> deposited at <math>T_s = 473\text{K}</math> (Magnification 18.98kX)</b>	<b>104</b>
<b>3.13(d) SEM photograph of a CdSe thin film of <math>t = 2000\text{\AA}</math> deposited at <math>T_s = 473\text{K}</math> (Magnification 20.98kX)</b>	<b>104</b>
<b>3.14 Typical EDAX pattern along with relative analysis of an 'as-deposited' CdSe thin film of <math>t = 2000\text{\AA}</math> deposited at elevated <math>T_s = 473\text{K}</math></b>	<b>105</b>

3.15(a) XRF spectra of an 'as-deposited' CdSe thin film showing $\text{SeK}_\beta$ and $\text{SeK}_{\alpha 1}$ lines along with two unknown peaks ( $T_s = 300\text{K}$ )	106
3.15(b) XRF spectra of an 'as-deposited' CdSe thin film showing peaks for $\text{SbK}_{\alpha 1}$ and $\text{CdK}_{\alpha 1}$ lines ( $T_s = 300\text{K}$ )	107
3.15(c) XRF spectra of an 'as-deposited' CdSe thin film showing $\text{ZrK}_{\alpha 1}$ and $\text{SeK}_\beta$ lines ( $T_s = 300\text{K}$ )	108
3.15(d) XRF spectra of an 'as-deposited' CdSe thin film showing $\text{SeL}_\alpha$ , $\text{MgK}_\alpha$ & $\text{NaK}_\alpha$ lines along with a small $\text{O-K}_\alpha$ and an unknown peak ( $T_s = 300\text{K}$ )	109

## CHAPTER IV

### Optoelectronic Properties of CdSe Thin Films 114-160

4.1(a) Dark current ( $I_D$ ) versus applied bias ( $V_a$ ) plot of a CdSe thin film of thickness ( $t = 2150\text{\AA}$ ) grown at room temperature ( $T_s = 300\text{K}$ )	120
4.1(b) Dark current ( $I_D$ ) versus applied bias ( $V_a$ ) plot of a CdSe thin film of thickness ( $t = 2000\text{\AA}$ ) grown at elevated temperature ( $T_s = 423\text{K}$ )	120
4.1(c) Dark current ( $I_D$ ) versus applied bias ( $V_a$ ) plot of a CdSe thin film of thickness ( $t = 2000\text{\AA}$ ) grown at elevated temperature ( $T_s = 473\text{K}$ )	121
4.1(d) Dark current ( $I_D$ ) versus applied bias ( $V_a$ ) plots at different ambient temperatures of a CdSe thin film ( $t = 1750\text{\AA}$ ) grown at $T_s = 473\text{K}$	121
4.2(a) Photocurrent ( $I_{ph}$ ) versus applied bias ( $V_a$ ) plots of a CdSe thin film grown at elevated $T_s$ illuminated by different monochromatic lights	123
4.2(b) Photocurrent ( $I_{ph}$ ) versus applied bias ( $V_a$ ) plots of a CdSe thin film grown at elevated $T_s$ illuminated by monochromatic light of 725 nm	123
4.2(c) Photocurrent ( $I_{ph}$ ) versus applied bias ( $V_a$ ) plots of CdSe thin films grown at different $T_s$ and illuminated by monochromatic light of 725nm	124
4.2(d) Photocurrent ( $I_{ph}$ ) versus applied bias ( $V_a$ ) plots of CdSe thin films grown at different $T_s$ and illuminated by monochromatic light of 725nm	124
4.2(e) Photocurrent ( $I_{ph}$ ) versus applied bias ( $V_a$ ) plots of CdSe thin films of different, $t$ , and illuminated by monochromatic light of 725nm	125
4.2(f) Photocurrent ( $I_{ph}$ ) versus applied bias ( $V_a$ ) plots of CdSe thin films	

of different, $t$ , and illuminated by monochromatic light of 725nm	125
4.3(a) $\ln J_{ph}$ versus $F^{1/2}$ plots of a CdSe thin film illuminated by different monochromatic lights of constant intensity	130
4.3(b) $\ln J_{ph}$ versus $F^{1/2}$ plots of a CdSe thin film illuminated by monochromatic light (725nm) of different intensities	130
4.3(c) $\ln J_{ph}$ versus $F^{1/2}$ plots of CdSe thin films grown at different $T_s$ , illuminated by monochromatic light (725nm)	131
4.3(d) $\ln J_{ph}$ versus $F^{1/2}$ plots of CdSe thin films grown at different $T_s$ , illuminated by monochromatic light (725nm)	131
4.3(e) $\ln J_{ph}$ versus $F^{1/2}$ plots of CdSe thin films of different thickness illuminated by monochromatic light (725nm)	132
4.3(f) $\ln J_{ph}$ versus $F^{1/2}$ plots of CdSe thin films of different thickness illuminated by monochromatic light (725nm)	132
4.4(a) $\ln I_{ph}$ versus $\Phi$ plots of a CdSe thin film illuminated by different monochromatic lights	136
4.4(b) $\ln I_{ph}$ versus $\Phi$ plots of a CdSe thin film at different applied bias voltages and illuminated by monochromatic light (725nm)	136
4.4(c) $\ln I_{ph}$ versus $\Phi$ plots of CdSe thin films grown at different $T_s$ and illuminated by monochromatic light (725nm)	137
4.4(d) $\ln I_{ph}$ versus $\Phi$ plots of CdSe thin films of different thickness and illuminated by monochromatic light (725nm)	137
4.4(e) $\ln I_{ph}$ versus $\Phi$ plots of a CdSe thin film at different applied bias voltages and illuminated by white light	138
4.4(f) $\ln I_{ph}$ versus $\Phi$ plots of CdSe thin films of different thickness and illuminated by white light	138
4.4(g) $\ln I_{ph}$ versus $\Phi$ plots of CdSe thin film grown at different $T_s$ and illuminated by white light	139
4.4(h) $\ln I_{ph}$ versus $\Phi$ plots of CdSe thin film grown at different $T_s$ and illuminated by white light	139
4.5(a) $\ln \sigma_D$ ( $\ln \sigma_L$ ) versus $1000/T$ plots of a CdSe thin film at dark and under different monochromatic illuminations	141

4.5(b)	$\ln\sigma_L$ versus $1000/T$ plots of a CdSe thin film illuminated by monochromatic light (725nm) of different intensities	141
4.5(c)	$\ln\sigma_L$ versus $1000/T$ plots of a CdSe thin film illuminated by monochromatic light (700nm) of different intensities	142
4.5(d)	$\ln\sigma_D$ versus $1000/T$ plots of a CdSe thin film at different applied bias voltages	142
4.5(e)	$\ln\sigma_D$ versus $1000/T$ plots of CdSe thin films having different thickness	143
4.5(f)	$\ln\sigma$ versus $1000/T$ plots of CdSe thin films grown at different $T_s$	143
4.6(a)	Variation of photosensitivity (S) with ambient temperature, T(K) under different monochromatic illuminations for a CdSe thin film ( $\Phi = 40$ lux)	148
4.6(b)	Variation of photosensitivity (S) with applied bias voltage, $V_a$ (V) under different monochromatic illuminations for a CdSe thin film ( $\Phi = 100$ lux)	148
4.7(a)	Variation of photoconductivity ( $\sigma_{ph}$ ) with grain size (D) of CdSe thin films of constant $t = 2000\text{\AA}$ and grown at different elevated $T_s$	149
4.7(b)	Variation of photoconductivity ( $\sigma_{ph}$ ) with grain size (D) of CdSe thin films of different, t, and grown at constant elevated $T_s = 473K$	149
4.8(a)	Variation of photoconductivity ( $\sigma_{ph}$ ) with strain ( $\epsilon$ ) of CdSe thin films of constant $t = 2000\text{\AA}$ grown at different elevated $T_s$	150
4.8(b)	Variation of photoconductivity ( $\sigma_{ph}$ ) with strain ( $\epsilon$ ) of CdSe thin films of different, t, and grown at constant elevated $T_s = 473K$	150
4.9(a)	Variation of Poole-Frekel coefficient ( $\beta_{PF}$ ) with grain size (D) of CdSe thin films of constant $t = 2000\text{\AA}$ and grown at different elevated $T_s$	151
4.9(b)	Variation of Poole-Frekel coefficient ( $\beta_{PF}$ ) with grain size (D) of CdSe thin films of different, t, and grown at constant elevated $T_s = 473K$	151
4.10(a)	Variation of Poole-Frekel coefficient ( $\beta_{PF}$ ) with strain ( $\epsilon$ ) of CdSe thin films of constant $t = 2000\text{\AA}$ and grown at different elevated $T_s$	152
4.10(b)	Variation of Poole-Frekel coefficient ( $\beta_{PF}$ ) with strain ( $\epsilon$ ) of CdSe thin films of different, t, and grown at constant elevated $T_s = 473K$	152
4.11(a)	Variation of photoconductivity ( $\sigma_{ph}$ ) with dislocation density ( $\delta$ ) of CdSe thin films of constant, $t = 2000\text{\AA}$ and grown at different elevated $T_s$	153
4.11(b)	Variation of photoconductivity ( $\sigma_{ph}$ ) with dislocation density ( $\delta$ ) of CdSe	

thin films of different, $t$ , and grown at constant elevated $T_s = 473K$	153
4.12(a) Variation of Poole-Frekel coefficient ( $\beta_{PF}$ ) with dislocation density ( $\delta$ ) of CdSe thin films of constant $t = 2000\text{\AA}$ and grown at different elevated $T_s$	154
4.12(b) Variation of Poole-Frekel coefficient ( $\beta_{PF}$ ) with dislocation density ( $\delta$ ) of CdSe thin films of different $t$ and grown at constant elevated $T_s = 473K$	154

## CHAPTER V

### Spectral Response, Rise & Decay of Photocurrent and Optical Properties 161-205

5.1(a) Spectral response characteristics of CdSe thin films of same thickness and grown at different elevated $T_s$	166
5.1(b) Spectral response characteristics of CdSe thin films of different thickness and grown at same elevated $T_s$	166
5.1(c) Spectral response characteristics at different applied bias of a CdSe thin film of constant thickness and grown at elevated $T_s$	167
5.1(d) Spectral response characteristics under different intensity of illuminations of a CdSe thin film of constant thickness and grown at elevated $T_s$	167
5.2 Rise & decay of photocurrent, $I_{ph}(t)$ , of photoconductor after turning on and off the light source	170
5.3(a) Growth and decay of photocurrent, $I_{ph}(t)$ , of a CdSe thin film grown at elevated $T_s$ and illuminated by monochromatic lights	172
5.3(b) Growth and decay of photocurrent, $I_{ph}(t)$ , of a CdSe thin film grown at elevated $T_s$ and illuminated by monochromatic lights	172
5.3(c) Growth and decay of photocurrent, $I_{ph}(t)$ , of a CdSe thin film grown at elevated $T_s$ and illuminated by monochromatic light (725nm)	173
5.3(d) Growth and decay of photocurrent, $I_{ph}(t)$ , of a CdSe thin film grown at elevated $T_s$ and illuminated by monochromatic light (725 nm)	173
5.4(a) Growth and decay of photocurrent, $I_{ph}(t)$ , of a CdSe thin	

film grown at elevated $T_s$ and illuminated by white light	174
5.4(b) Growth and decay of photocurrent, $I_{ph}(t)$ , of a CdSe thin film grown at elevated $T_s$ and illuminated by white light	174
5.4(c) Growth and Decay of photocurrent, $I_{ph}(t)$ , of a CdSe thin film grown at elevated $T_s$ , illuminated by white light, at an ambient temperature 333K	175
5.4(d) Growth and decay of photocurrent, $I_{ph}(t)$ , of a CdSe thin film grown at elevated $T_s$ , illuminated by white light, at an ambient temperature 363K	175
5.5(a) $\ln(I_0/I_t)$ versus time plot of a CdSe thin film grown at elevated $T_s$ and illuminated by monochromatic light	178
5.5(b) $\ln(I_0/I_t)$ versus time plot of a CdSe thin film grown at elevated $T_s$ and illuminated by monochromatic light	178
5.5(c) $\ln(I_0/I_t)$ versus time plot of a CdSe thin film grown at elevated $T_s$ and illuminated by monochromatic light (725nm)	179
5.5(d) $\ln(I_0/I_t)$ versus time plot of a CdSe thin film grown at elevated $T_s$ under different bias voltages and illuminated by monochromatic light (725nm)	179
5.6(a) $\ln(I_0/I_t)$ versus time plot of a CdSe thin film grown at elevated $T_s$ and illuminated by white light	180
5.6(b) $\ln(I_0/I_t)$ versus time plot of a CdSe thin film grown at elevated $T_s$ and illuminated by white light	180
5.6(c) $\ln(I_0/I_t)$ versus time plot of a CdSe thin film grown at elevated $T_s$ and illuminated by white light, at an ambient temperature 333K	181
5.6(d) $\ln(I_0/I_t)$ versus time plot of a CdSe thin film grown at elevated $T_s$ and illuminated by white light, at an ambient temperature 363K	181
5.7(a) Plot of trap depths ( $E_1$ ) versus ambient temperature ( $T$ ) at different intensity of illuminations of a CdSe thin film grown at elevated $T_s$	186
5.7(b) Plot of trap depths ( $E_2$ ) versus ambient temperature ( $T$ ) at different intensity of illuminations of a CdSe thin film grown at elevated $T_s$	186
5.8(a) Density of states ( $N_{eff}$ ) versus intensity of illumination ( $\Psi$ ) at room temperature of a CdSe thin film grown at elevated $T_s$	187
5.8(b) Density of states ( $N_{eff}$ ) versus intensity of illumination ( $\Psi$ ) at different ambient temperatures of a CdSe thin film grown at elevated $T_s$	187



<b>5.9(a) Frequency factor (S) versus intensity of illumination (<math>\Psi</math>) at room temperature of a CdSe thin film grown at elevated <math>T_s</math></b>	<b>188</b>
<b>5.9(b) Frequency factor (S) versus intensity of illumination (<math>\Psi</math>) at different ambient temperature of a CdSe thin film grown at elevated <math>T_s</math></b>	<b>188</b>
<b>5.10(a) Trap depth (<math>E_1</math>) versus intensity of illumination (<math>\Psi</math>) at room temperature of a CdSe thin film grown at elevated <math>T_s</math></b>	<b>189</b>
<b>5.10(b) Trap depth (<math>E_2</math>) versus intensity of illumination (<math>\Psi</math>) at room temperature of a CdSe thin film grown at elevated <math>T_s</math></b>	<b>189</b>
<b>5.11(a) Trap depth (<math>E_1</math>) versus intensity of illumination (<math>\Psi</math>) at different ambient temperature of a CdSe thin film grown at elevated <math>T_s = 473K</math></b>	<b>190</b>
<b>5.11(b) Trap depth (<math>E_2</math>) versus intensity of illumination (<math>\Psi</math>) at different ambient temperature of a CdSe thin film grown at elevated <math>T_s = 473K</math></b>	<b>190</b>
<b>5.12(a) Transmission and absorbance spectra of a CdSe thin film (<math>t = 2100\text{\AA}</math>) grown at elevated <math>T_s = 523K</math></b>	<b>195</b>
<b>5.12(b) Transmission and absorbance spectra of a CdSe thin film (<math>t = 2100\text{\AA}</math>) grown at elevated <math>T_s = 473K</math></b>	<b>195</b>
<b>5.13(a) Transmission spectra of a CdSe thin film sample grown at elevated <math>T_s = 523K</math> and of thickness, <math>t = 4950\text{\AA}</math></b>	<b>196</b>
<b>5.13(b) Transmission spectra of a CdSe thin film grown at elevated <math>T_s = 523K</math> and of thickness, <math>t = 3860\text{\AA}</math></b>	<b>196</b>
<b>5.14(a) <math>n</math> versus <math>1/\lambda^2</math> plot of a CdSe thin film of <math>t = 4950\text{\AA}</math>, <math>T_s = 573K</math></b>	<b>198</b>
<b>5.14(b) Variation of refractive index (<math>n</math>) with wavelength of a CdSe thin film of <math>t = 4950\text{\AA}</math>, <math>T_s = 573K</math></b>	<b>198</b>
<b>5.14(c) Variation of extinction coefficient (<math>k</math>) with wavelength of a CdSe thin film of <math>t = 4950\text{\AA}</math>, <math>T_s = 573K</math></b>	<b>199</b>
<b>5.15(a) The <math>(\alpha hv)^2</math> vs photon energy <math>hv</math> plots of CdSe thin films of constant thickness <math>t = 2000\text{\AA}</math> and grown at different elevated <math>T_s</math></b>	<b>199</b>
<b>5.15(b) The <math>(\alpha hv)^2</math> vs photon energy <math>hv</math> plots for a few CdSe films of different thickness and grown at constant elevated <math>T_s = 473K</math></b>	<b>200</b>